

Supporting Information

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Understanding Carbon Nanotube-Based Ionic Diodes: Design and Mechanism

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Table of contents

- SI-1 Parameters applied in the numerical simulation
- SI-2 Fabrication and characterization of the MWCNT-based ionic diode
- SI-3 Summary of ICR performance of selective ionic diodes reported since 2006
- SI-4 Numerical simulation results of reservoir size, applied voltage and electroosmotic flow effects on the performance of the MWCNT-based ionic diode
- SI-5 Numerical simulation results of Debye length and diameter with respect to ICR ratio
- SI-6 Numerical simulation results of channel length effects and the charge modification length effects on the performance of the MWCNT-based ionic diode
- SI-7 KCl concentration effects on the performance of the MWCNT-based ionic diode
- SI-8 Polyelectrolyte concentration effects on the performance of the MWCNT-based ionic diode

SI-1 Parameters applied in the numerical simulation

 Table S1 Constants and parameters.

Parameter	Description	Value and unit		
μ	Viscosity of electrolyte solution	$0.9 \times 10^{-3} [Pa*s]$		
ρ	Density of electrolyte solution	1000 [kg/m^3]		
$arepsilon_r$	Dielectric constant of water	80[1]		
$oldsymbol{arepsilon}_0$	Permittivity of vacuum	$8.854 \times 10^{-12} \text{ [F/m]}$		
$c_{i^{\infty}}$	Bulk concentration	1[mol/m^3]		
e	Unit charge	$1.602 \times 10^{-19} [C]$		
F	Faraday Constant	9649 [C/mol]		
D_1	Diffusion coefficient of K ⁺	$1.957 \times 10^{-9} \text{ [m^2/s]}$		
D_2	Diffusion coefficient of Cl ⁻	$2.032 \times 10^{-9} \text{ [m^2/s]}$		
R	Gas constant	8.314[J/mol/K]		
k_b	Boltzmann constant	$1.381 \times 10^{23} [J/K]$		
T	Temperature	298[K]		

SI-2 Fabrication and characterization of the MWCNT-based ionic diode

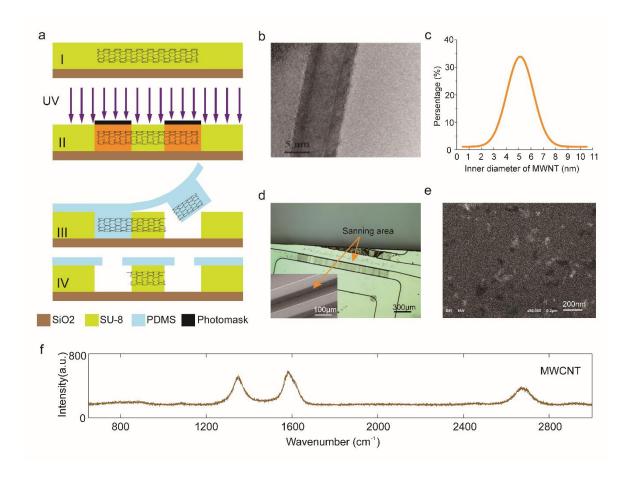


Figure S1 (a) Flow diagram of fabricating CNT nanofluidic chips. (I) Embedding a CNT into a photoresist layer. (II) UV exposure to generate microchannel network. (III) Mechanical avulsion of MWCNT by using PDMS elastomer. (IV) Ready-to-use MWCNT nanofluidic chip after plasma-assisted bonding. (b) TEM image of a MWCNT used for the device fabrication and (c) the inner diameter of the MWCNTs used in this work. (d) Samples for characterizing the MWCNT openings after mechanical avulsion. (e) SEM image of the opening of the MWCNT after mechanical avulsion. (f) Raman shifts of a MWCNT forest.

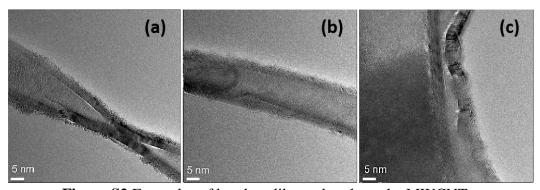


Figure S2 Examples of bamboo-like nodes along the MWCNTs.

SI-3 Summary of ICR performance of selective ionic didoes reported since 2006

Table S2 Summary of ICR ratio of ionic diodes created in recent years specifically based on different nanostructures, conical nanopores, $^{1-11}$ nanomembranes $^{12-24}$ and nanochannels $^{25-31}$ since 2006, in which the nanopore-based ionic diodes are made from polyethylene terephthalate (PET) 1,4,6,8,11 , polydimethylsiloxane (PDMS), 2,7 polyimide (PI), 10 silicic solid-state materials, 3,5,9 the nanomembrane-based ionic diodes are developed on hydrogels, 13,19,21 cellulose, 24 graphite oxide (GO), 12,15 combinations of polyelectrolyte-based nanomembranes and nanopores, 14,18,20,22,23 and Janus polyelectrolyte nanomembranes (PENM), 16,17 the nanochannel-based ionic diodes are fabricated by Al_2O_3/SiO_2 , 25,26,30 PET 29,31 and CNT. 27,28

	Materials	Working	Rectification	Year
Conical	PET	±5V	5 4	2011
nanopore/nanochannel	PET	±5V	217 1	2006
-	PET	±5V	300 11	2010
	PET	±0.9V	65 ⁶	2010
	PET	±2V	68	2015
	PDMS	±1V	2 7	2016
	PDMS/nanoparticles	±10V	55^{2}	2007
	Polyimide (PI)	±2V	27 10	2009
	Silicon nitride (Si3N4)	±3V	1.9 5	2016
	Silicon	±3V	2 3	2010
	Borosilicate glass	±1V	15 ⁹	2019
Nanomembrane	Gel (PDAC/PSS)	±5V	40 13	2010
	Gel/SiO2	±5V	38000 19	2018
	Hydrogel	±5V	9 21	2017
	PDAC/PSS/CNT composite	_		
	Cellulose	±5V	15 ²⁴	2019
	Porous bock polymer/PET nanopore	±2V	1075 ²³	2017
	PIM-EA-TB/PET micropore	±1V	180 ²⁰	2014
	Porous bock polymer/PAA nanopore	±2V	489 ²²	2018
	Nafion/PET micropore	±0.5V	30 14	2017
	Mesoporous carbon/microporous	±2V	450 18	2016
	Nafion/PIM-EA-TB	±1V	64 17	2016
	PES-Py/PAEK-HS	±2V	57.2 16	2015
	SP-GO	±1V	48 12	2007
	n-Go/p-GO	±2V	5.9 ¹⁵	2012
	·			
Straight nanochannel	Al2O3/SiO2	±1V	300 ²⁶	2009
C	Alumina	±0.2V	12 25	2009
	Al2O3/SiO2	±5V	4.5^{30}	2012
	PET (Dumbbell shaped)	±2V	75 ²⁹	2016
	PET (Conical pore/nanochannel)	±2V	553 ³¹	2009
	CNT	$\pm 0.5V$	18 ²⁷	2013
	CNT	±0.45V	6 ²⁸	2018
	CNT	±5V	1481.5	This work

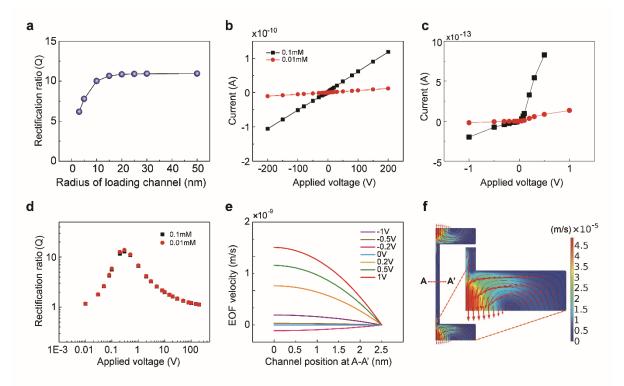


Figure S3 (a) Channel reservoir size effect on the performance of the MWCNT-based ionic diode. The reservoir size affects the ICR performance; however, the effect vanishes when the diameter of the reservoir is larger than 20 nm in radius. In the modelling, the reservoir was 25 nm in radius through this paper. (b) Simulation I-V curves of a MWCNT-based ionic diode working in the range of -200 V to 200 V but with different ionic concentrations of 0.1 mM and 0.01 mM, and (c) a zoomed-in view of the I-V curves working in the range of -1 V to 1 V. (d) Rectification ratio of the I-V curves in (b). (e) Profiles of electroosmotic flow (EOF) velocity at the channel cross-section A-A' marked in (f). (f) Streamlines and arrow-plot of EOF in the nanochannel. In the simulations, a nanochannel of 50 nm long, 5 nm in diameter was applied for all the cases.

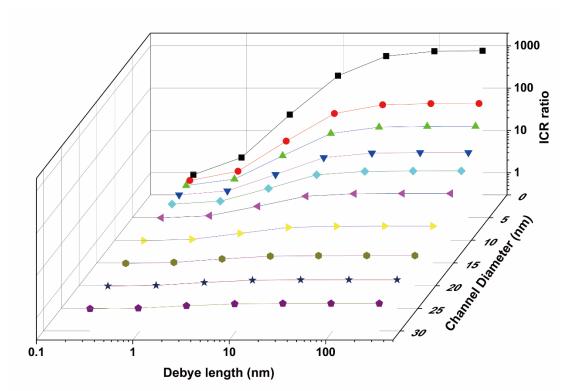


Figure S4 Phase diagram of the Debye length and the channel diameter with respect to the ICR ratio.

SI-6 Numerical simulation results of channel length effects and the charge modification length effects on the performance of the MWCNT-based ionic diode

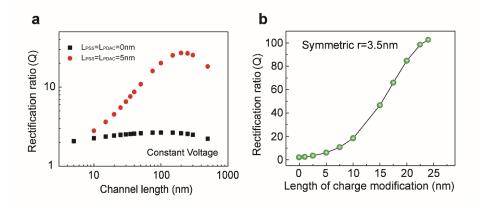


Figure S5 (a) Channel length effects on the ICR performance of the CNT ionic diode working at constant voltages of ± 1 V. The 50 nm long nanochannel was filled with 0.1 mM KCl solution and modified with 5 nm long charges of ± 2 mC⁻² at the channel terminals. (b) Numerical simulation results of ICR performance of the CNT ionic diode constructed by using a channel of 7 nm in diameter. The numerical model is the same as the one used in the channel length effect study demonstrated in the main text (**Figure 3e**) except for the channel diameter.

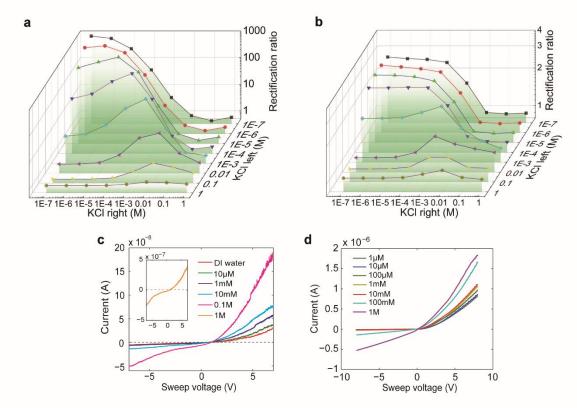


Figure S6 Numerical simulation results of KCl concentration effects on the performance of the MWCNT-based ionic diode of (a) $L_{PSS} = L_{PDAC} = 24$ nm and (b) $L_{PSS} = L_{PDAC} = 0$ nm modification length. The simulation models are the same as that of the KCl concentration-effect model demonstrated in **Figure 4a** of the main text but with different charge modification lengths. Experimental I-V curves of (c) the symmetric and (d) the asymmetric cases.

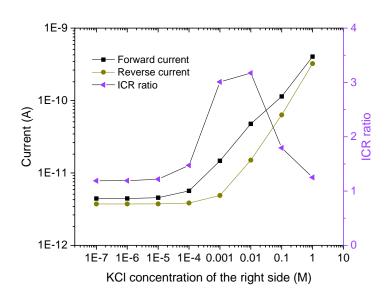


Figure S7 Forward current, reverse current and ICR ratio of the ionic diode working with 10 mM KCl in left side channel and various concentrations of KCl solution in the left side.

SI-8 Charge density/polyelectrolyte concentration effects on the performance of the MWCNT-based ionic diode

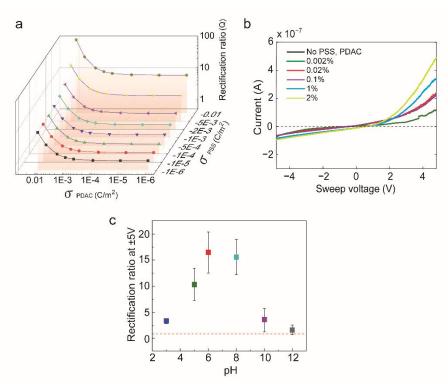


Figure S8 Density of charge modification affects the performance of the MWCNT-based ionic diode. (a) Numerical simulation results of charge density effects on the performance of the ionic diode under the condition of $L_{PSS} = L_{PDAC} = 0$ nm. (b) A family of I-V curves of a MWCNT-based ionic diode working with symmetric concentration of polyelectrolytes (the case of **Figure 5**b). (c) The effects of pH level of the KCl solutions. In the experiments, the microchannels were filled with 1 mM KCl solution containing 1% PDAC or 1% PSS.

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